

Varying Cu-Ti hybridization near the Fermi energy in Cu_xTiSe_2 : Results from supercell calculations.

T. Jeong and T. Jarlborg

DPMC, University of Geneva, 24 Quai Ernest-Ansermet, CH-1211 Geneva 4, Switzerland

The properties of Cu_xTiSe_2 are studied by band structure calculation based on the density functional theory for supercells. The density-of-states (DOS) for $x=0$ has a sharply raising shoulder in the neighborhood of the Fermi energy, E_F , which can be favorable for spacial charge modulations. The Cu impurity adds electrons and brings the DOS shoulder below E_F . Hybridization makes the Ti-d DOS at E_F , the electron-phonon coupling and the Stoner factor very large. Strong pressure dependent properties are predicted from the calculations, since the DOS shoulder is pushed to higher energy at a reduced lattice constant. Effects of disorder are also expected to be important because of the rapidly varying DOS near E_F .

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The layered TiSe_2 compound is much studied because of the appearance of charge density waves (CDW). The ground state is believed to be either a semimetal or a semiconductor with a small indirect gap[1, 2, 3]. From photoemission experiments it is concluded that the CDW transition consists of a change in electronic structure from a small indirect gap into a state with a larger indirect gap at a slightly different location in the Brillouin zone[4]. Recently Morosan *et al.*[5] reported that a continuous intercalation of TiSe_2 with Cu is possible, where the Cu atoms enter between the TiSe_2 layers to yield Cu_xTiSe_2 , with solubility of Cu up to $x \approx 0.11$. The CDW transition is continuously suppressed, and a superconducting state appears near $x = 0.04$ with a maximum T_c of 4.15 K at $x = 0.08$. A CDW superconductivity phase diagram as a function of doping is developed for Cu_xTiSe_2 , analogous to the antiferromagnetism-superconductivity phase diagram found for the high temperature superconductors.

In this work we investigate the electronic structure of Cu_xTiSe_2 for $x=0$ and $x \approx 0.08$ based on the density functional theory applied to supercell calculations. As will be shown, one of the main results is that Cu doping introduces electronic charge carriers, leading to high-DOS properties, which partly confirms the interpretation of experimental results [5].

TiSe_2 has the layered CdI_2 crystal structure. Planes of titanium atoms are surrounded by planes of selenium atoms, forming a sandwich structure, where the selenium atoms are arranged in octahedral coordination around the titanium atoms at $z = \pm \frac{1}{4}$. The unit cells are arranged so that the metal atoms are stacked directly above each other. The TiSe_2 layers are well separated and bound by van der Waals interaction. As Cu atoms are added, they occupy positions within these open spaces between the TiSe_2 layers. This results in a systematic expansion of the unit cell with increasing Cu content in Cu_xTiSe_2 . The experimental lattice constants are $a = 6.7$ a.u. and $c = 11.35$ a.u. when x is near 0.08 [5].

The self-consistent Linear Muffin-Tin Orbital method [6, 7] is applied to a 48-site supercell in which one Cu

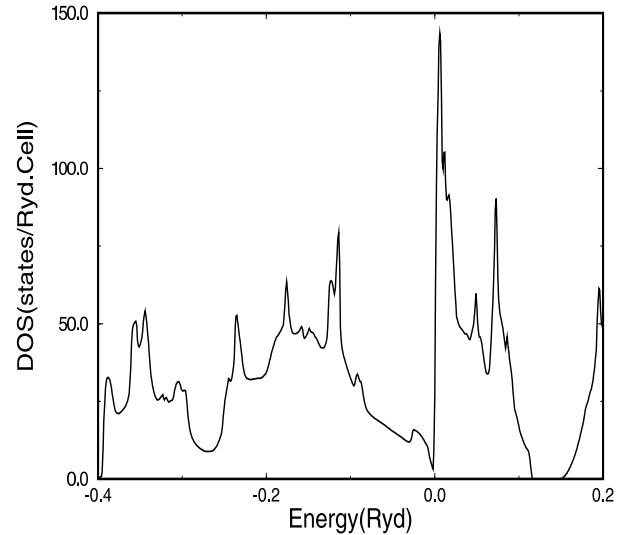


FIG. 1: The total density of states of TiSe_2 . The energy is relative to E_F .

atom is intercalated between two Se layers. In these calculations we use a potential based on the local density approximation (LDA) [8], with no special on-site correction due to correlation. The cell consists of $\text{CuTi}_{12}\text{Se}_{24}$ and 11 empty spheres in the open space separating the TiSe_2 layers. The repeat distance between Cu atoms is 2 unit cells in the two plane directions and 3 cells along $\hat{z}$. This is chosen to minimize the Cu-to-Cu interactions within a reasonably simple unit cell for a Cu concentration x of 0.0833, which is close to the concentration for optimal T_c . The self-consistent iterations use initially 8 k -points in the irreducible Brillouin Zone, while they are terminated by iterations using 75 k -points. The Wigner-Seitz sphere radii are 2.88 a.u. for Ti and 3.17 a.u. for Se respectively. The basis-set for the atoms includes d-states in the direct basis and f states as tail contribution. The direct basis for empty spheres includes p, with d states

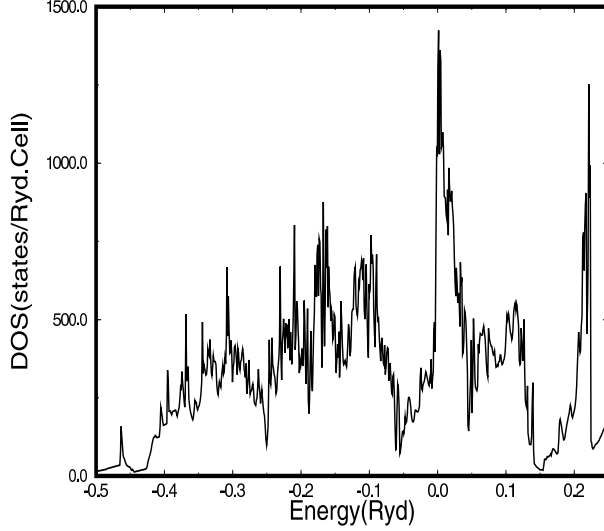


FIG. 2: The total density of states of $\text{CuTi}_{12}\text{Se}_{24}$ at the lattice constant 6.7 a.u.. The energy is relative to E_F .

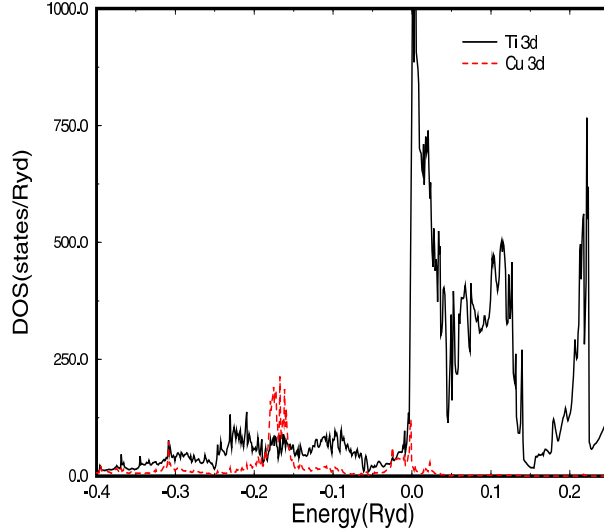


FIG. 3: The projected Ti-3d and Cu-3d parts of the total DOS shown in fig. 2.

in the tails. The bands are calculated at the experimental lattice constant, and at two smaller volumes, for the case with optimal Cu insertion. It should be recalled that LDA typically underestimates the lattice constant by 1-3 percent for 3d metals.

The supercell is repeated periodically and effects of random disorder, of distortion around the impurity, or of higher order periodicities among the Cu atoms are not included. It should be noted that any disorder (structural or substitutional) within the supercell will intro-

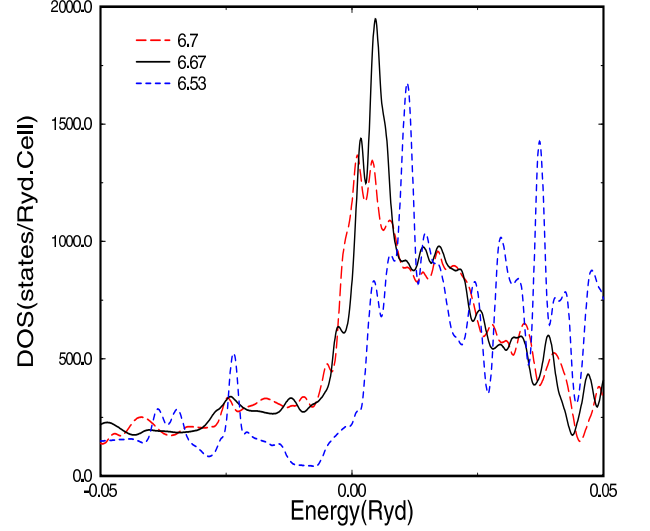


FIG. 4: The total density of states of $\text{CuTi}_{12}\text{Se}_{24}$ near E_F (at zero energy in each case) at three different lattice constants .

duce band broadening in general, since degenerate bands of the perfectly repeated supercell will be lifted. These effects of disorder are likely to be more important for this particular system, because of the very sharp DOS structures near E_F .

The electron-phonon coupling λ is calculated using the Rigid-Ion approximation and experimental information of the phonon moment $\langle \omega^2 \rangle$. As the Debye temperature for TiSe_2 is not known to us, we use an average Debye temperatures of NbSe_2 (280 K [9]) and TiS_2 (235 K [10]). The modification of the pure phonon contribution to λ due to the additions of Cu is probably not very important. Since the DOS is large on Ti, it is expected that the electronic contribution will be dominated by these sites. The pressure variation of the phonon moment is scaled through the calculated variation of the Bulk modulus. These procedures are not very precise, but they should be sufficient for getting insight of the contributions to λ [11].

The Stoner factor, $\bar{S}$, is calculated from the paramagnetic band results in the standard way, by assuming a finite rigid-band splitting due to exchange of all bands [12]. If there is only one band contributing to $N(E_F)$, one can write $\bar{S} = N \cdot I$, where I is an exchange integral for that band. The DOS is dominated by the Ti-d band and the Stoner factor is mainly because of Ti-d electrons. Hybridization with other bands, and the induced exchange splitting on other sites, is likely to reduce the effective Stoner enhancement, but spin-polarized calculations would be needed to verify this.

The DOS for the primitive cell of undoped TiSe_2 is shown in Fig. 1. An independent calculation using the Full Potential Local Orbital (FPLO) [13] method, using a potential based on the gradient corrected density func-

tional [14], gives a similar band structure, but with a slightly larger dispersion of a band above E_F , so that the first unoccupied DOS peak becomes less prominent. The band results indicate that the pure material is a semimetal where E_F is in a valley in the DOS, with a low value of $N(E_F)$ of 10-20 states per Ryd per TiSe₂. The uncertainty is due to the fact that E_F falls slightly on the right hand side of the minimum of the DOS (see Fig. 1), on the steep shoulder, where the DOS increases rapidly with energy. This is for the perfect structure without disorder or CDW.

A simple rigid-band model for a potential (or charge) modulation in a material with an increasing DOS near E_F (as for pure TiSe₂) can be shown to favor CDW. Shifts of the local DOS functions relative to E_F suggest that some regions of the material should get a high local $N(E_F)$ because of the large DOS just above E_F . Oppositely, other regions where the potential is repulsive will have E_F closer to the local "gap" with minimum DOS. A similar reasoning as for a Peierls transition show that the total kinetic energy will be lowered by such a splitting of local states. Namely, since the DOS is sharply raising at E_F and the number of states is conserved we find that an upward shift, δ_u , of the DOS relative to E_F within the regions that loose electrons will be larger than the downward shift, δ_d , of the DOS within the region that gain electrons. If the average DOS to the left and right side are N_u and N_d , respectively, and Δn is the number of transferred electrons, we have that $\Delta n = \delta_u \cdot N_u = \delta_d \cdot N_d$. But the kinetic energy will be $\frac{1}{2}\Delta n(\delta_d - \delta_u)$, i.e., negative. Or equivalently, the total (kinetic) energy will be lower for the CDW state. If, by electron doping, E_F moves to higher energy on a linearly increasing DOS, then the relative difference between N_u and N_d will be smaller, and the gain in kinetic energy and the tendency for CDW formation will diminish.

Total energy contributions from the Coulomb interactions and hybridization are neglected here, but the model gives a hint that a sufficiently raising DOS near E_F is favorable for CDW. Nothing can be said about the periodicity of these waves from the model. However, from qualitative arguments it is expected that modulations with long wave lengths are more probable, since they have lower costs in terms of hybridization energy. It can also be noted that irregular regions of up- and down-

shifted potentials, as for long-range disorder, will be favored through the same type of energy gains as for CDW. Supercell calculations with some guidance for probable CDW modulations would be needed to solve this problem. It is generally believed that Fermi surface nesting is not a determining factor for the k-vector of the CDW [4].

When Cu is inserted it acts as an electron dopant. Cu brings along d-states near E_F , which hybridize strongly with the Ti-d band, and the total DOS at E_F increases very much as can be seen in Fig. 2. From an inspection of the local Ti DOS functions it can be verified that the Ti close to the Cu site has the highest $N(E_F)$ values. The total Cu-d and the sum of all Ti-d DOS functions are shown in Fig. 3.

The DOS peak near E_F is high and narrow. This makes any calculation of $N(E_F)$ dependent properties very sensitive to small shifts of E_F (non-stoichiometry) and to band broadening (disorder effects). The energy derivative of $N(E_F)$ is high, by shifting E_F 2 mRy to lower energies, N can be reduced by a factor of two.

Nevertheless, by using the unshifted unbroadened band results we obtain a very large Stoner enhancement, $S = 1/(1 - \bar{S})$, see table I. Ferromagnetism is expected when $\bar{S}$ is larger than one. Apart from non-stoichiometry and disorder effects it is possible that the impurity-like electronic structure with a large DOS near the Cu site will overestimate the calculation of $\bar{S}$. The reason is that the exchange splitting is assumed to be equal on all sites in the model, while in reality this may cost additional kinetic energy on sites with low DOS. A spin-polarized calculation would give a better answer, but it has not been attempted at this stage because of the very slow convergence for the supercell.

The calculated values of λ are reasonable and not as extreme as could be expected from the large DOS and $\bar{S}$. The main contribution to λ comes from the Ti atoms. The Ti-DOS is large, but there is only a moderate dipole scattering contribution to the electronic part of λ , because the total DOS is dominated by the d-character (Typically 98 percent of the Ti-DOS is of d-character).

A surprising effect is the large variation of $N(E_F)$ with pressure, P . Two calculations at smaller lattice constants show clearly that the narrow peak of the Cu-d state moves sensitively with volume. This state is hybridized with the Ti-d band so that also the Ti-d DOS

TABLE I: The calculated parameters of CuTi₁₂Se₂₄. The Debye temperature θ_D is from experiment and scaled through the calculated volume dependence. The units of γ is (mJ/mol K²), and $N(E_F)$ is in units of states per (Ryd·cell).

a_0 (a.u.)	λ	$T_c(K)$	S	γ	$\theta_D(K)$	$N(E_F)$
6.7	1.52	20.2	1.31	11.13	240	1220
6.67	0.37	0.11	1.09	4.75	250	960
6.53	0.21	0.01	0.49	1.26	290	290

TABLE II: D-DOS at E_F on Cu and Ti near (Ti_{Cu}) and far from (Ti) the Cu impurity. The units of $N(E_F)$ are states per (Ryd·atom)

a_0 (a.u.)	Cu d $N(E_F)$	Ti _{Cu} - d $N(E_F)$	Ti- d $N(E_F)$
6.7	22.1	127.	63.0
6.67	19.	72.	41.
6.53	0.85	28.1	1.0

at E_F will vary much with volume. A downward shift of this peak by about 5 mRy is found when the lattice constant is increased from 6.67 to 6.7 a.u.. If the lattice constant is reduced to 6.53 a.u. there will be an upward shift of the DOS edge to a location above E_F and the total $N(E_F)$ is not much larger than for pure TiSe₂. The charges on Cu and Ti increases with P at the expense of charge on Se. The effect is that the Cu-d band becomes more filled for a uniform reduction of volume. The peak in the DOS 20 mRy below E_F for the smallest lattice constant, is mainly a Cu-d state. The Ti-d DOS is too far away in energy to hybridize with this state, and at E_F there will be less Cu-d to Ti-d hybridization. This will result in a reduction of $N(E_F)$. An inspection of the local Ti-DOS for the smallest lattice constant reveals an important proximity effect near the Cu site. The Ti-d DOS at E_F is of the order 28 states/Ry/atom on each of the 8 Ti on the layers closest to Cu. But in the more distant Ti layer, where there are 4 Ti atoms, the local Ti-d DOS at E_F is only of the order 1-2 states/Ry per atom, which is like the case for pure TiSe₂. The reason is that the local Ti-d DOS is pushed just above E_F for these sites. In the calculations for the two larger lattice constants the local Ti-d DOS values at E_F are comparable between all Ti sites, also within the most distant layer. This shows that the properties of Cu doped TiSe₂ will be very sensitive because of the exact position of the DOS shoulder relative to E_F .

These calculations are made for perfect scaling of the supercell lattice. Thus no effects of possible rearrangement of the Cu occupations, different c/a ratio or disorder are taken into account. If such effects are small, one can expect strong P -variations of the properties. According to our calculations the system would pass from ferromagnetism, towards exchange enhanced paramagnetism, through a region with superconductivity and large electron phonon coupling, and finally to a fairly low-DOS material when the volume is reduced by about 8 percent only. However, this unusual sensitivity is caused by a sharp DOS shoulder which is passing through E_F , and therefore one can also expect large error bars. As mentioned before, disorder and different Cu impurity distributions can be important and have a moderating effect on the P -dependence.

More hybridization with the Ti- p and f bands is needed for a larger λ . By reducing the lattice constant it is possible to increase the hybridization and the electronic contribution to λ , but the effect is masked by the changes in total $N(E_F)$, which is decreasing much at large pressure. In addition, fine structures in the peaked DOS add some noise to the evolution of N with pressure.

An estimation of the superconducting T_C from the calculated electron-phonon coupling via the McMillan equation gives reasonable values in line with observations, see Table I. However, some reduction is expected from spin-fluctuations, especially since the calculations indicate large exchange enhancement. The calculated electronic specific heat constant, γ , includes the enhancement for electron-phonon coupling, but not from possible spin fluctuations. At the largest lattice constant γ is considerably larger than the measured value, about 4.5 mJ/mol K² [5]. The calculated result for γ at the intermediate volume agrees best with experiment, but the electron-phonon coupling is rather low at the same volume. Again, this is an indication that disorder in the real material will reduce the effective DOS at E_F and increase hybridization.

In conclusion, we find that undoped TiSe₂ is a low-DOS material with semi-metallic properties, but the DOS is rapidly increasing near E_F . The latter fact is probably important for the properties of pure and doped TiSe₂. For instance, the kinetic contribution to the total energy will be lowered by spacial modulations of the potential as produced by a CDW or disorder. Electron doping, accompanied by disorder, will put E_F closer to the broadened DOS peak. This should weaken the mechanism for CDW formation, while the material soon becomes a high-DOS material. The local Ti-d DOS at E_F for a supercell of Cu doped TiSe₂ is increased very much through hybridization with the Cu-impurity and its d-band. The exact value of $N(E_F)$ is uncertain because of the sharp structure of the DOS near E_F , which is found both for pure TiSe₂ and the supercell, and it depends probably also on Cu ordering. The estimation of λ show that conventional superconductivity based on electron-phonon coupling is probable, with a T_C of the order of a few K. Despite the changes in electronic structure, from a low DOS semi-metal in pure TiSe₂ to a high DOS material at high Cu doping, it is the Ti states that makes λ large. Some results, like the large Stoner factor, indicate that disorder in the real material is important to moderate the very large $N(E_F)$. Effects of disorder will increase hybridization and can make λ larger even if the total DOS is lowered. The particular situation with E_F near a shoulder in the DOS, and electron doping via Cu-impurities, turns out to give strong volume dependence of $N(E_F)$ in addition to the dependence on x . Further work is needed to sort out the precise effects of disorder, but it can already be predicted that not only variations of x , but also P -variations, will be determining for the properties of Cu _{x} TiSe₂.

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